



## CSD16556Q5B 25-V N-Channel NexFET™ Power MOSFET

### 1 Features

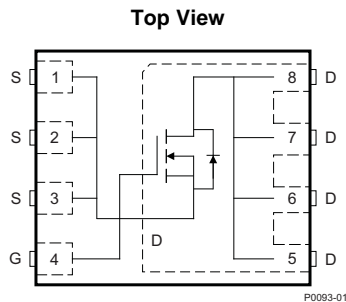
- Extremely Low Resistance
- Ultralow  $Q_g$  and  $Q_{gd}$
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm x 6-mm Plastic Package

### 2 Applications

- Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems
- Optimized for Synchronous FET Applications

### 3 Description

This 25 V, 0.9 m $\Omega$ , 5 x 6 mm SON NexFET™ power MOSFET is designed to minimize losses in synchronous rectification and other power conversion applications.



### Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE		UNIT
$V_{DS}$	Drain-to-Source Voltage	25		V
$Q_g$	Gate Charge Total (4.5 V)	36		nC
$Q_{gd}$	Gate Charge Gate-to-Drain	12		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 4.5\text{ V}$	1.2	m $\Omega$
		$V_{GS} = 10\text{ V}$	0.9	m $\Omega$
$V_{GS(th)}$	Threshold Voltage	1.4		V

### Ordering Information<sup>(1)</sup>

Device	Media	Qty	Package	Ship
CSD16556Q5B	13-Inch Reel	2500	SON 5 x 6 mm Plastic Package	Tape and Reel
CSD16556Q5BT	7-Inch Reel	250		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

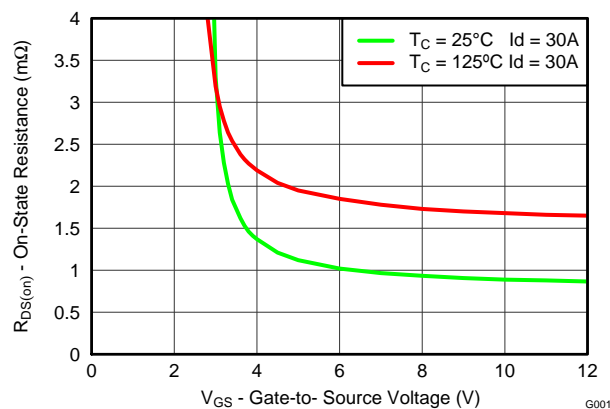
### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	25	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current (Package limited)	100	A
	Continuous Drain Current (Silicon limited), $T_C = 25^\circ\text{C}$	263	
	Continuous Drain Current <sup>(1)</sup>	40	
$I_{DM}$	Pulsed Drain Current <sup>(2)</sup>	400	A
$P_D$	Power Dissipation <sup>(1)</sup>	3.2	W
	Power Dissipation, $T_C = 25^\circ\text{C}$	191	
$T_J$ , $T_{stg}$	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$E_{AS}$	Avalanche Energy, single pulse $I_D = 103\text{ A}$ , $L = 0.1\text{ mH}$ , $R_G = 25\text{ }\Omega$	530	mJ

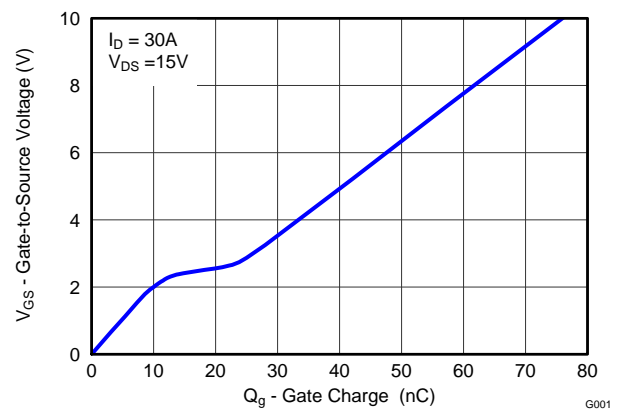
(1) Typical  $R_{\theta JA} = 40^\circ\text{C/W}$  on 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Max  $R_{\theta JC} = 1.3^\circ\text{C/W}$ , Pulse duration  $\leq 100\text{ }\mu\text{s}$ , duty cycle  $\leq 1\%$

**$R_{DS(on)}$  vs  $V_{GS}$**



**Gate Charge**



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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision B (January 2013) to Revision C</b>	<b>Page</b>
• Added part number to title .....	<b>1</b>
• Added 7 inch reel in Ordering Information .....	<b>1</b>
• Increase max pulsed current to 400 A .....	<b>1</b>
• Added line for max power dissipation with case temperature held to 25°C .....	<b>1</b>
• Updated pulsed current conditions .....	<b>1</b>
• Updated <a href="#">Figure 1</a> to a normalized $R_{\theta JC}$ curve .....	<b>4</b>
• Updated the SOA in <a href="#">Figure 10</a> .....	<b>6</b>
• Updated the mechanical drawing and dimensions table .....	<b>8</b>

<b>Changes from Revision A (December 2012) to Revision B</b>	<b>Page</b>
• Changed $g_{fs}$ , Transconductance TYP value From: 2 S To: 191 S .....	<b>3</b>

<b>Changes from Original (November 2012) to Revision A</b>	<b>Page</b>
• Changed the device from product preview to: Production .....	<b>1</b>

## 5 Specifications

### 5.1 Electrical Characteristics

(T<sub>A</sub> = 25°C unless otherwise stated)

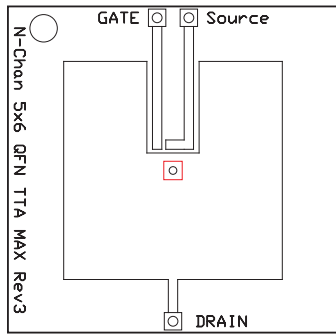
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV <sub>DSS</sub>	Drain-to-Source Voltage	V <sub>GS</sub> = 0 V, I <sub>DS</sub> = 250 μA	25			V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V			1	μA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA
V <sub>GS(th)</sub>	Gate-to-Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 250 μA	1.2	1.4	1.7	V
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 4.5 V, I <sub>DS</sub> = 30 A		1.2	1.5	mΩ
		V <sub>GS</sub> = 10 V, I <sub>DS</sub> = 30 A		0.9	1.07	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15 V, I <sub>DS</sub> = 30 A		191		S
DYNAMIC CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1MHz		4750	6180	pF
C <sub>oss</sub>	Output Capacitance			2270	2950	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			220	280	pF
R <sub>G</sub>	Series Gate Resistance			0.7	1.4	Ω
Q <sub>g</sub>	Gate Charge Total (4.5 V)	V <sub>DS</sub> = 15 V, I <sub>DS</sub> = 30 A		36	47	nC
Q <sub>gd</sub>	Gate Charge Gate-to-Drain			12		nC
Q <sub>gs</sub>	Gate Charge Gate-to-Source			11		nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>			7		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V		45		nC
t <sub>d(on)</sub>	Turn On Delay Time	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>DS</sub> = 30 A, R <sub>G</sub> = 2 Ω		17		ns
t <sub>r</sub>	Rise Time			34		ns
t <sub>d(off)</sub>	Turn Off Delay Time			25		ns
t <sub>f</sub>	Fall Time			13		ns
DIODE CHARACTERISTICS						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 30 A, V <sub>GS</sub> = 0 V		0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 15 V, I <sub>F</sub> = 30 A, di/dt = 300 A/μs		84		nC
t <sub>rr</sub>	Reverse Recovery Time			41		ns

### 5.2 Thermal Information

(T<sub>A</sub> = 25°C unless otherwise stated)

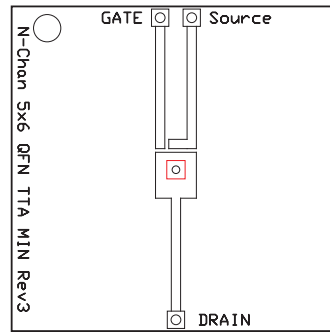
THERMAL METRIC		MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction-to-Case Thermal Resistance <sup>(1)</sup>			1.3	°C/W
R <sub>θJA</sub>	Junction-to-Ambient Thermal Resistance <sup>(1)(2)</sup>			50	

- (1) R<sub>θJC</sub> is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inches × 1.5-inches (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



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Max  $R_{\theta JA} = 50^{\circ}\text{C/W}$   
 when mounted on  
 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of  
 2-oz. (0.071-mm thick)  
 Cu.

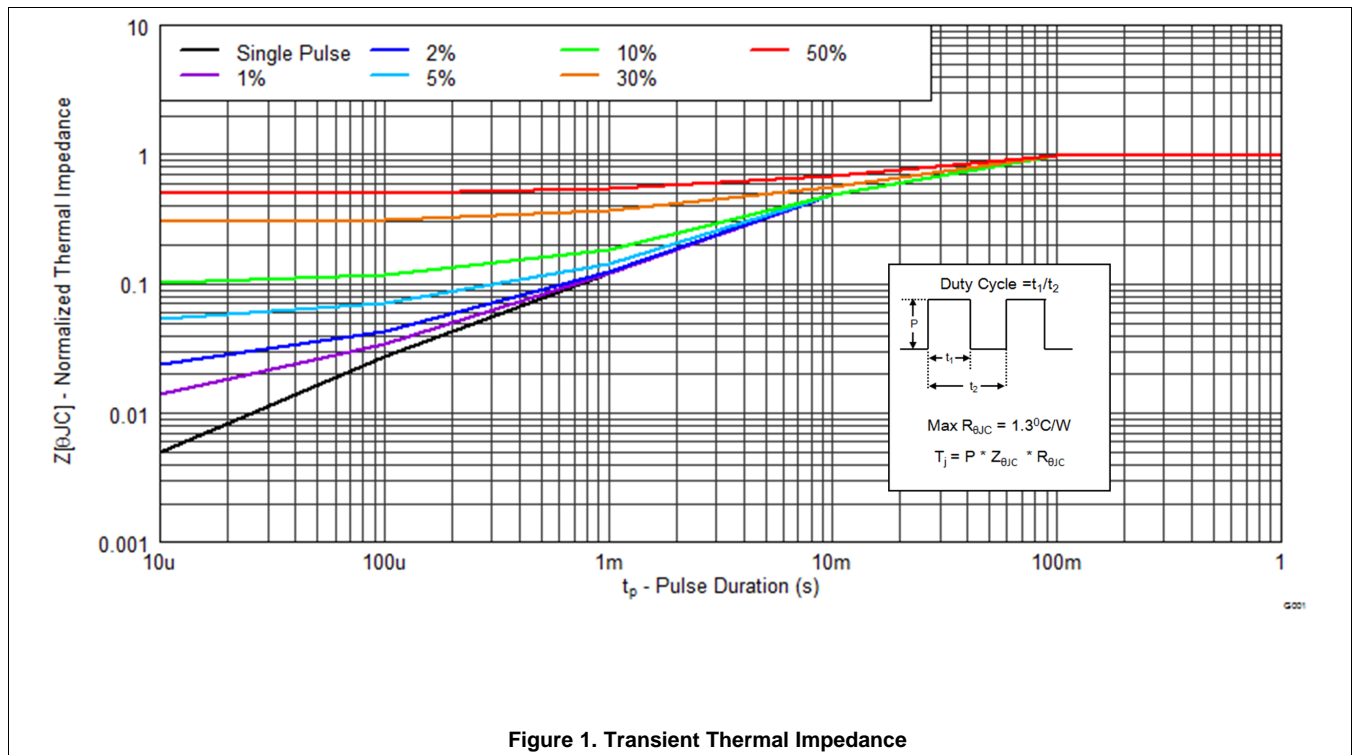


M0137-02

Max  $R_{\theta JA} = 125^{\circ}\text{C/W}$   
 when mounted on a  
 minimum pad area of  
 2-oz.  
 (0.071-mm thick) Cu.

### 5.3 Typical MOSFET Characteristics

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)



## Typical MOSFET Characteristics (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

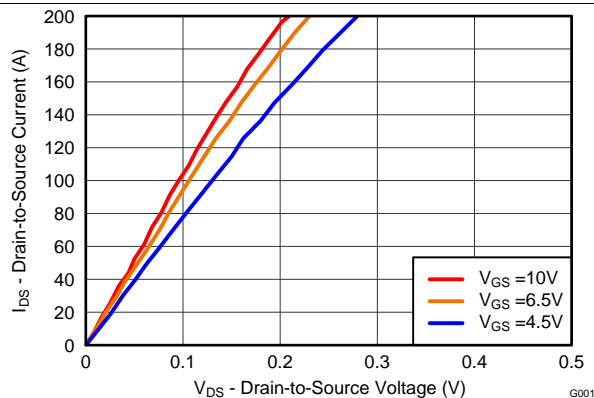


Figure 2. Saturation Characteristics

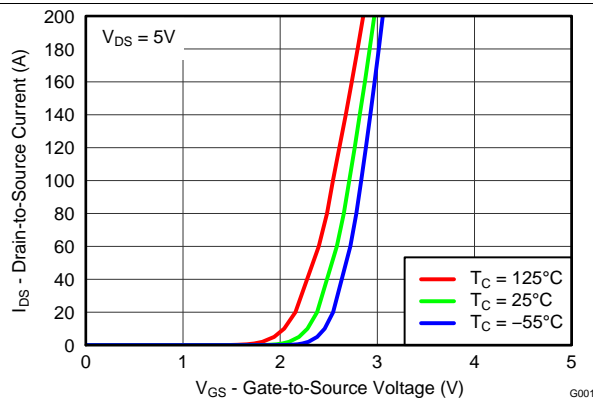


Figure 3. Transfer Characteristics

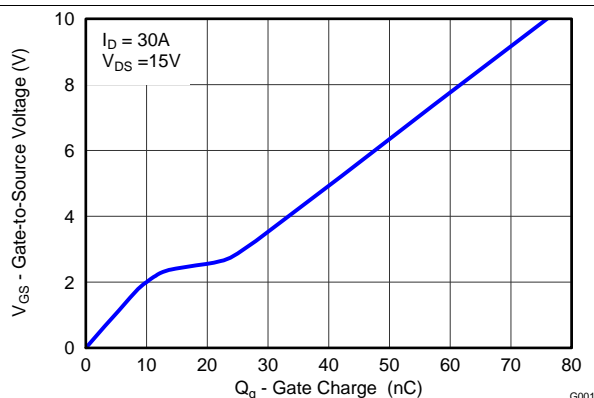


Figure 4. Gate Charge

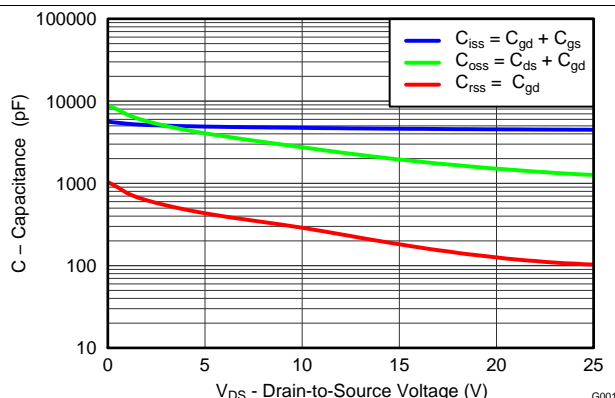


Figure 5. Capacitance

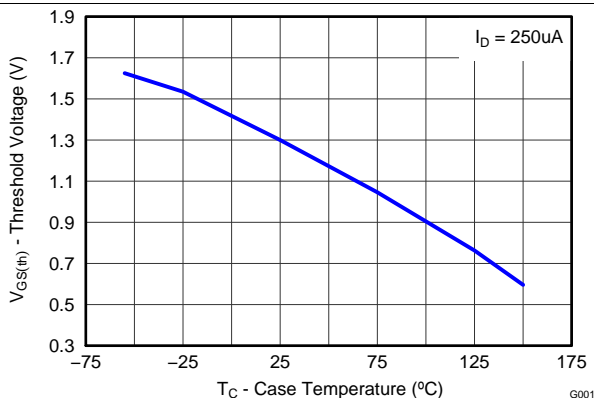


Figure 6. Threshold Voltage vs Temperature

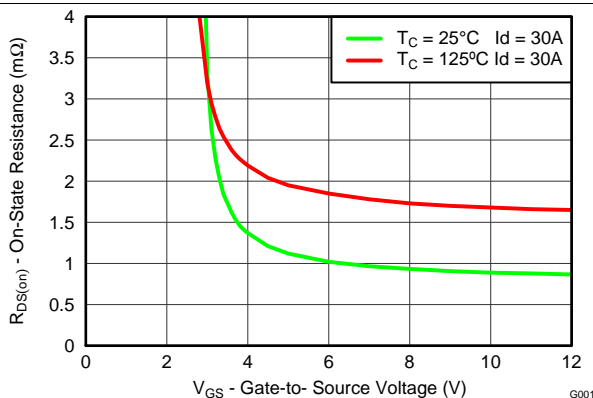


Figure 7. On-State Resistance vs Gate-to-Source Voltage

## Typical MOSFET Characteristics (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

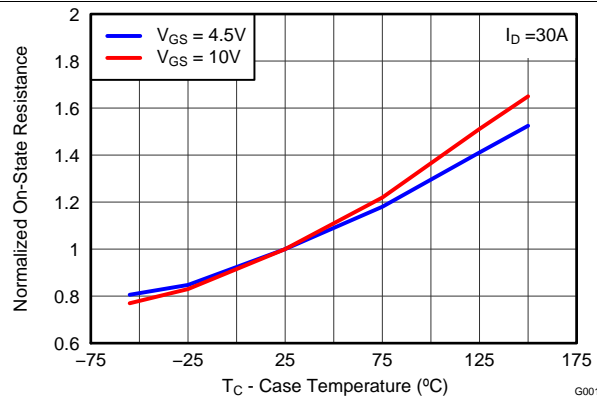


Figure 8. Normalized On-State Resistance vs Temperature

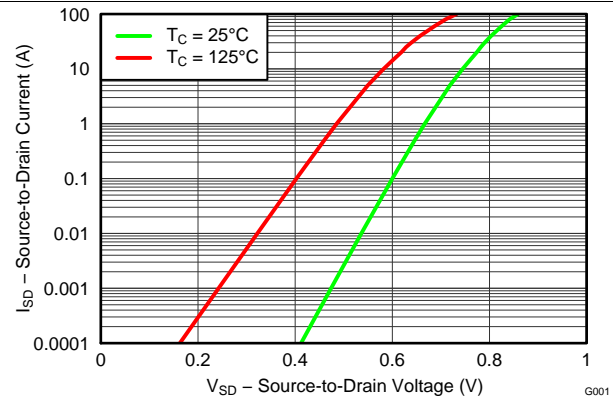


Figure 9. Typical Diode Forward Voltage

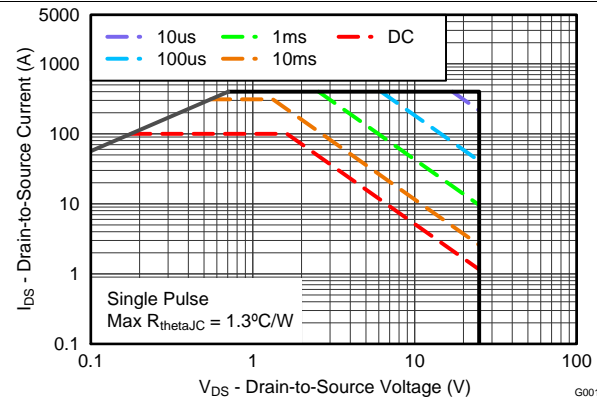


Figure 10. Maximum Safe Operating Area (SOA)

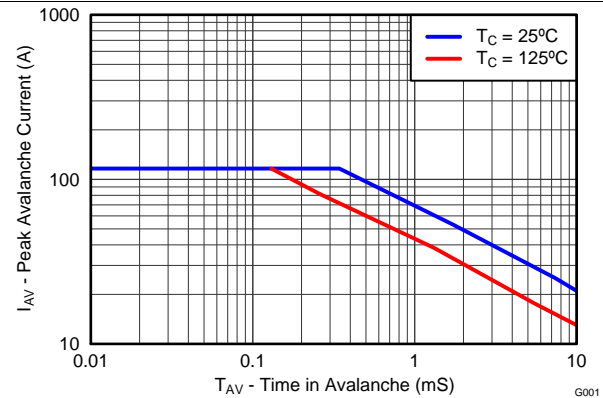


Figure 11. Single Pulse Unclamped Inductive Switching

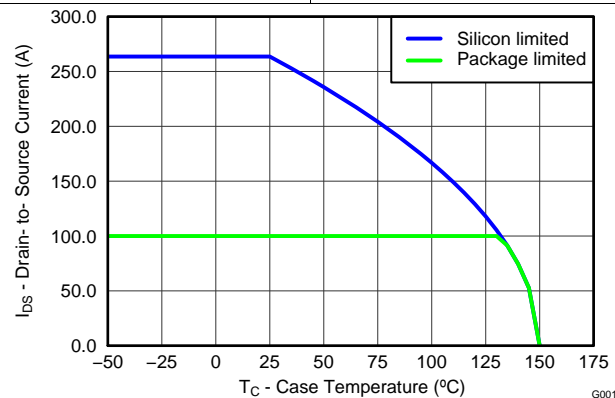


Figure 12. Maximum Drain Current vs Temperature

## 6 Device and Documentation Support

### 6.1 Trademarks

NexFET is a trademark of Texas Instruments.  
All other trademarks are the property of their respective owners.

### 6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 6.3 Glossary

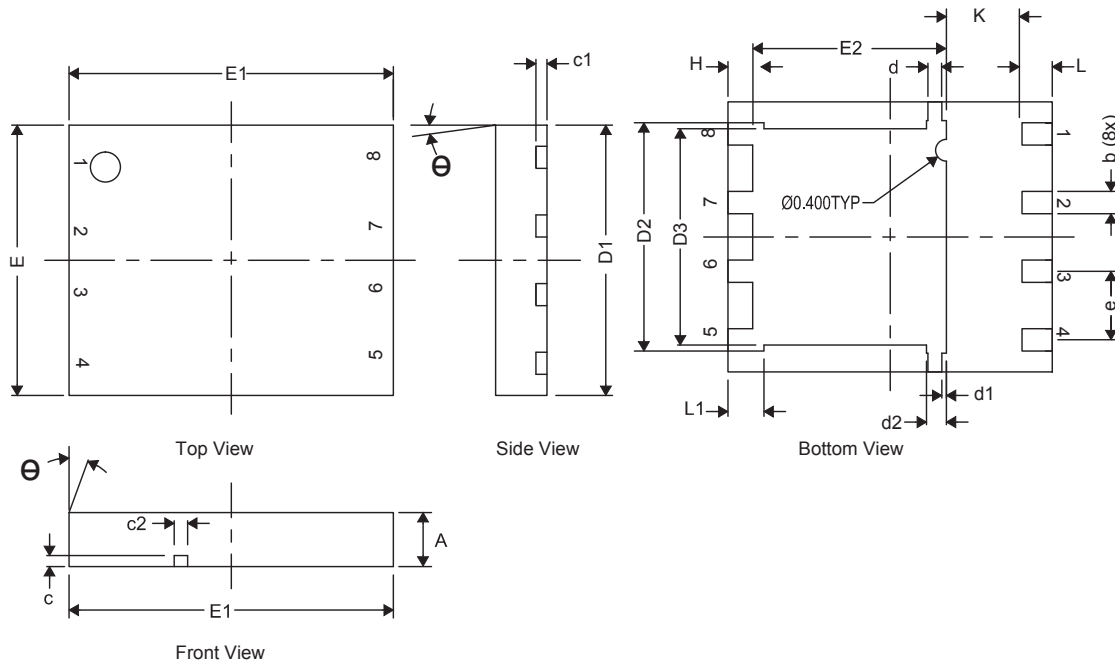
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

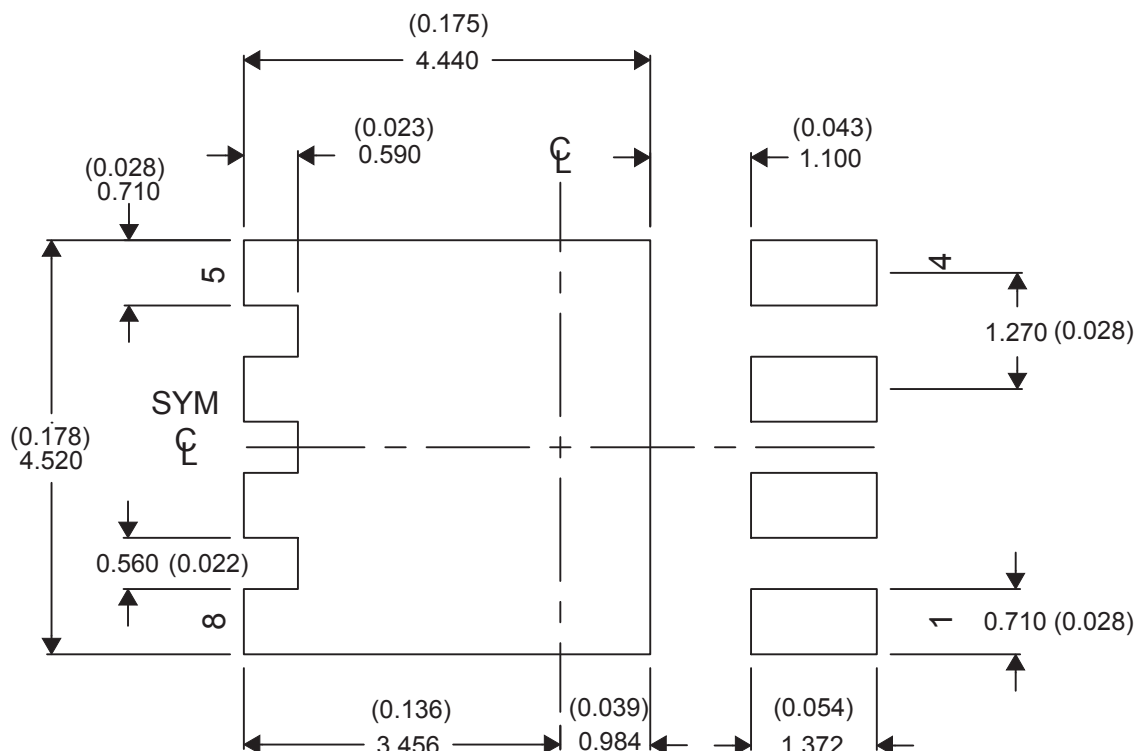
### 7.1 Q5B Package Dimensions



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.80	1.00	1.05
b	0.36	0.41	0.46
c	0.15	0.20	0.25
c1	0.15	0.20	0.25
c2	0.20	0.25	0.30
D1	4.90	5.00	5.10
D2	4.12	4.22	4.32
D3	3.90	4.00	4.10
d	0.20	0.25	0.30
d1	0.085 TYP		
d2	0.319	0.369	0.419
E	4.90	5.00	5.10
E1	5.90	6.00	6.10
E2	3.48	3.58	3.68
e	1.27 TYP		
H	0.36	0.46	0.56
L	0.46	0.56	0.66
L1	0.57	0.67	0.77
$\theta$	0°	—	—
K	1.40 TYP		

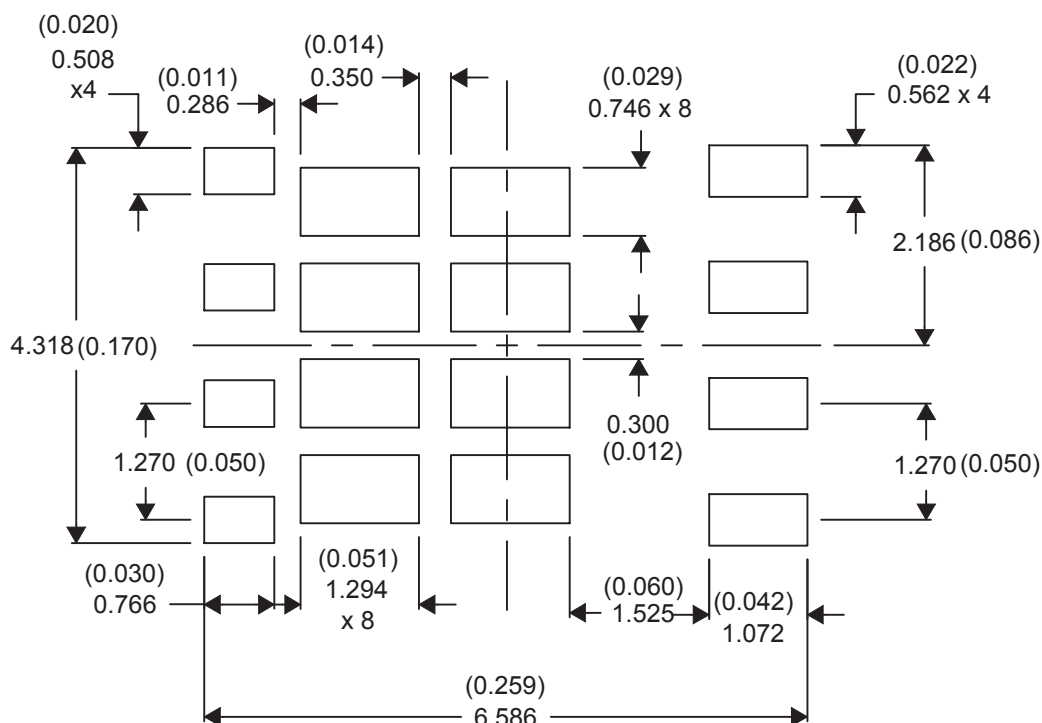


## 7.2 Recommended PCB Pattern

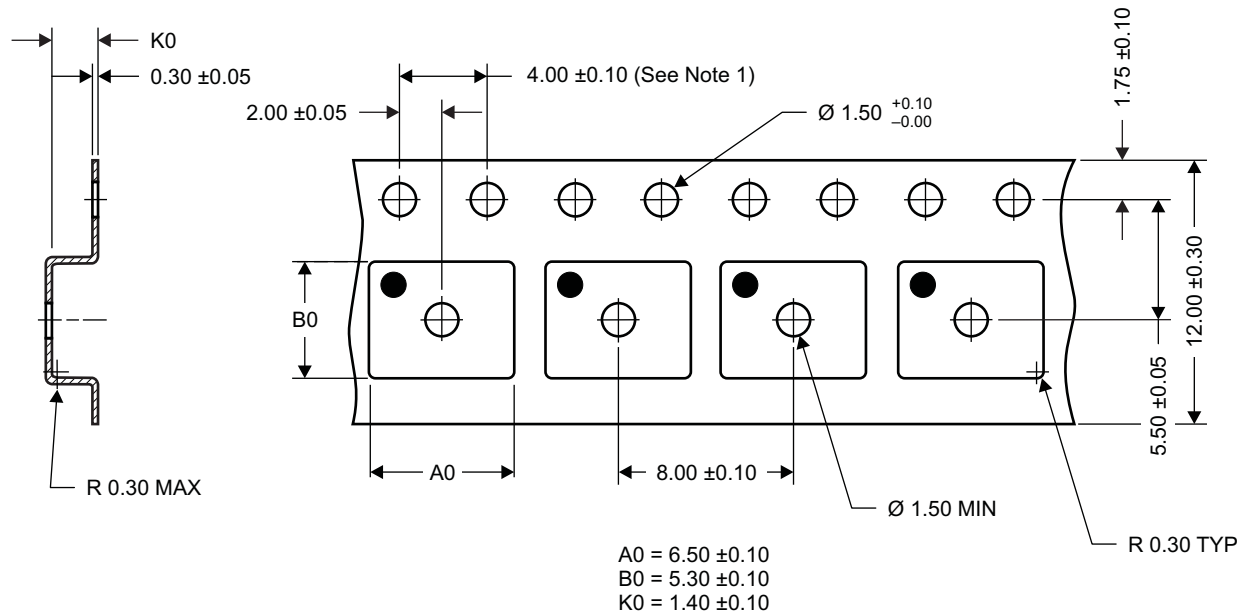


For recommended circuit layout for PCB designs, see application note [SLPA005](#) – *Reducing Ringing Through PCB Layout Techniques*.

## 7.3 Recommended Stencil Pattern



## 7.4 Q5B Tape and Reel Information



M0138-01

### Notes:

1. 10-sprocket hole-pitch cumulative tolerance  $\pm 0.2$
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified).
5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD16556Q5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16556	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16556Q5B	VSON-CLIP	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16556Q5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0

## IMPORTANT NOTICE

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### Products

Audio	<a href="http://www.ti.com/audio">www.ti.com/audio</a>
Amplifiers	<a href="http://amplifier.ti.com">amplifier.ti.com</a>
Data Converters	<a href="http://dataconverter.ti.com">dataconverter.ti.com</a>
DLP® Products	<a href="http://www.dlp.com">www.dlp.com</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
Clocks and Timers	<a href="http://www.ti.com/clocks">www.ti.com/clocks</a>
Interface	<a href="http://interface.ti.com">interface.ti.com</a>
Logic	<a href="http://logic.ti.com">logic.ti.com</a>
Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>
Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>
OMAP Applications Processors	<a href="http://www.ti.com/omap">www.ti.com/omap</a>
Wireless Connectivity	<a href="http://www.ti.com/wirelessconnectivity">www.ti.com/wirelessconnectivity</a>

### Applications

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